MMBT5550

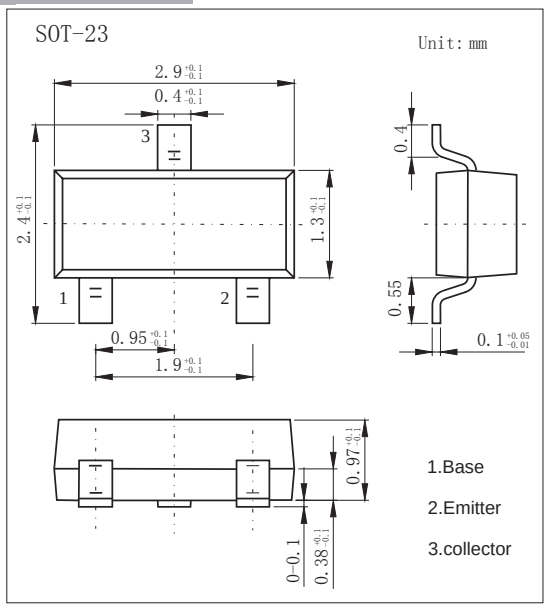
SOT-23 Plastic-Encapsulate Transistors

Features

- Collector Current Capability I_C=0.6A
- Collector Emitter Voltage V_{CEO}=140V
- High Voltage Transistor
- NPN Transistors

MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	160	V
Collector - Emitter Voltage	V_{CEO}	140	
Emitter - Base Voltage	V_{EBO}	6	
Collector Current - Continuous	I_C	0.6	A
Collector Power Dissipation	P_C	225	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	556	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{stg}	-55 to 150	

PACKAGE INFORMATION

Device	Package	Shipping
MMBT5550	SOT-23	3000/Tape&Reel

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= 100 μA， I_E= 0	160			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= 1 mA， I_B= 0	140			
Emitter - base breakdown voltage	V_{EBO}	I_E= 100 μ A， I_C= 0	6			
Collector-base cut-off current	I_{CBO}	V_{CB}= 100 V , I_E= 0			100	nA
Emitter cut-off current	I_{EBO}	V_{EB}= 4V , I_C=0			50	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=10 mA, I_B=1mA			0.15	V
		I_C=50 mA, I_B=5mA			0.25	
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=10 mA, I_B=1mA			1	
		I_C=50 mA, I_B=5mA			1.2	
DC current gain	h_{FE}	V_{CE}= 5V, I_C= 1mA	60			
		V_{CE}= 5V, I_C= 10mA	60		250	
		V_{CE}= 5V, I_C= 50mA	20			

Note.: Pulse test: pulse width ≤300μs, duty cycle≤ 2.0%.

■ Marking

Marking	M1F